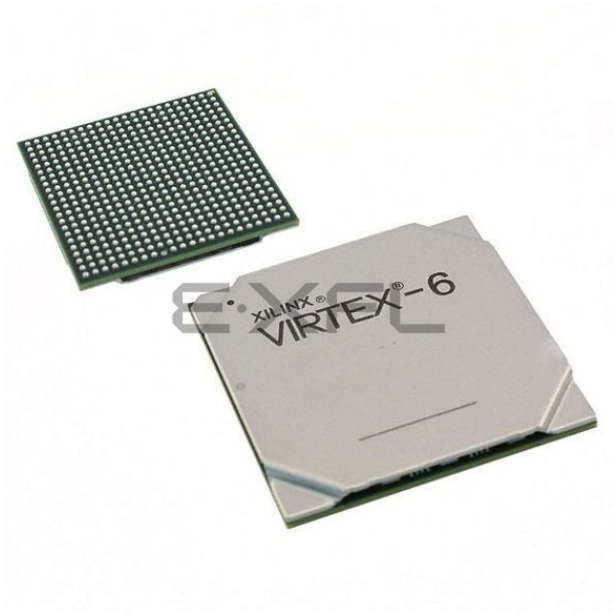
AMD Xilinx - XC6VLX130T-L1FF784I Datasheet



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Details	
Product Status	Active
Number of LABs/CLBs	10000
Number of Logic Elements/Cells	128000
Total RAM Bits	9732096
Number of I/O	400
Number of Gates	-
Voltage - Supply	0.91V ~ 0.97V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	784-BBGA, FCBGA
Supplier Device Package	784-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc6vlx130t-l1ff784i

Table 2: **Recommended Operating Conditions**

Symbol	Description	Min	Max	Units
V_{CCINT}	Internal supply voltage relative to GND for all devices except -1L devices.	0.95	1.05	V
	For -1L commercial temperature range devices: internal supply voltage relative to GND, T_j = 0°C to +85°C	0.87	0.93	V
	For -1L industrial temperature range devices: internal supply voltage relative to GND, T_j = –40°C to +100°C	0.91	0.97	V
V_{CCAUX}	Auxiliary supply voltage relative to GND	2.375	2.625	V
V_{CCO}(1)(2)(3)	Supply voltage relative to GND	1.14	2.625	V
V_{IN}	2.5V supply voltage relative to GND	GND – 0.20	2.625	V
	2.5V and below supply voltage relative to GND	GND – 0.20	V_{CCO} + 0.2	V
I_{IN}(5)	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	10	mA
V_{BATT}(6)	Battery voltage relative to GND	1.0	2.5	V
V_{FS}(7)	External voltage supply for eFUSE programming	2.375	2.625	V
T_j	Junction temperature operating range for commercial (C) temperature devices	0	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	100	°C
	Junction temperature operating range for military (M) temperature devices	–55	125	°C

Notes:

1. Configuration data is retained even if V_{CCO} drops to 0V.
2. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, and 2.5V.
3. The configuration supply voltage V_{CC_CONFIG} is also known as V_{CCO_0}.
4. All voltages are relative to ground.
5. A total of 100 mA per bank should not be exceeded.
6. V_{BATT} is required only when using bitstream encryption. If battery is not used, connect V_{BATT} to either ground or V_{CCAUX}.
7. During eFUSE programming, V_{FS} must be within the recommended operating range and T_j = +15°C to +85°C. Otherwise, V_{FS} can be connected to GND.

Table 6: **Power Supply Ramp Time**

Symbol	Description	Ramp Time	Units
V_{CCINT}	Internal supply voltage relative to GND	0.20 to 50.0	ms
V_{CCO}	Output drivers supply voltage relative to GND	0.20 to 50.0	ms
V_{CCAUX}	Auxiliary supply voltage relative to GND	0.20 to 50.0	ms

SelectIO™ DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 7: **SelectIO DC Input and Output Levels**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
LVCMOS25, LVDCI25	–0.3	0.7	1.7	V_{CCO} + 0.3	0.4	V_{CCO} – 0.4	Note(3)	Note(3)
LVCMOS18, LVDCI18	–0.3	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.3	0.45	V_{CCO} – 0.45	Note(4)	Note(4)
LVCMOS15, LVDCI15	–0.3	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.3	25% V_{CCO}	75% V_{CCO}	Note(4)	Note(4)
LVCMOS12	–0.3	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.3	25% V_{CCO}	75% V_{CCO}	Note(5)	Note(5)
HSTL I_12	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	V_{CCO} + 0.3	25% V_{CCO}	75% V_{CCO}	6.3	6.3
HSTL I(2)	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	V_{CCO} + 0.3	0.4	V_{CCO} – 0.4	8	–8
HSTL II(2)	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	V_{CCO} + 0.3	0.4	V_{CCO} – 0.4	16	–16
HSTL III(2)	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	V_{CCO} + 0.3	0.4	V_{CCO} – 0.4	24	–8
DIFF HSTL I(2)	–0.3	50% V_{CCO} – 0.1	50% V_{CCO} + 0.1	V_{CCO} + 0.3	–	–	–	–
DIFF HSTL II(2)	–0.3	50% V_{CCO} – 0.1	50% V_{CCO} + 0.1	V_{CCO} + 0.3	–	–	–	–
SSTL2 I	–0.3	V_{REF} – 0.15	V_{REF} + 0.15	V_{CCO} + 0.3	V_{TT} – 0.61	V_{TT} + 0.61	8.1	–8.1
SSTL2 II	–0.3	V_{REF} – 0.15	V_{REF} + 0.15	V_{CCO} + 0.3	V_{TT} – 0.81	V_{TT} + 0.81	16.2	–16.2
DIFF SSTL2 I	–0.3	50% V_{CCO} – 0.15	50% V_{CCO} + 0.15	V_{CCO} + 0.3	–	–	–	–
DIFF SSTL2 II	–0.3	50% V_{CCO} – 0.15	50% V_{CCO} + 0.15	V_{CCO} + 0.3	–	–	–	–
SSTL18 I	–0.3	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.3	V_{TT} – 0.47	V_{TT} + 0.47	6.7	–6.7
SSTL18 II	–0.3	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.3	V_{TT} – 0.60	V_{TT} + 0.60	13.4	–13.4
DIFF SSTL18 I	–0.3	50% V_{CCO} – 0.125	50% V_{CCO} + 0.125	V_{CCO} + 0.3	–	–	–	–
DIFF SSTL18 II	–0.3	50% V_{CCO} – 0.125	50% V_{CCO} + 0.125	V_{CCO} + 0.3	–	–	–	–
SSTL15	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	V_{CCO} + 0.3	V_{TT} – 0.175	V_{TT} + 0.175	14.3	14.3

Notes:

1. Tested according to relevant specifications.
2. Applies to both 1.5V and 1.8V HSTL.
3. Using drive strengths of 2, 4, 6, 8, 12, 16, or 24 mA.
4. Using drive strengths of 2, 4, 6, 8, 12, or 16 mA.
5. Supported drive strengths of 2, 4, 6, or 8 mA.
6. For detailed interface specific DC voltage levels, see UG361: *Virtex-6 FPGA SelectIO Resources User Guide*.

HT DC Specifications (HT_25)

Table 8: **HT DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OD}	Differential Output Voltage for XC devices	R_T = 100 Ω across Q and $\overline{Q}$ signals	480	600	885	mV
	Differential Output Voltage for XQ devices		480	600	930	mV
ΔV_{OD}	Change in V_{OD} Magnitude		–15	–	15	mV
V_{OCM}	Output Common Mode Voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	440	600	760	mV
ΔV_{OCM}	Change in V_{OCM} Magnitude		–15	–	15	mV
V_{ID}	Input Differential Voltage		200	600	1000	mV
ΔV_{ID}	Change in V_{ID} Magnitude		–15	–	15	mV
V_{ICM}	Input Common Mode Voltage		440	600	780	mV
ΔV_{ICM}	Change in V_{ICM} Magnitude		–15	–	15	mV

LVDS DC Specifications (LVDS_25)

Table 9: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.825	–	–	V
V_{ODIFF}	Differential Output Voltage (Q – $\overline{Q}$), Q = High (Q – $\overline{Q}$), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage for XC devices	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.075	1.250	1.425	V
	Output Common-Mode Voltage for XQ devices		1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q – $\overline{Q}$), Q = High (Q – $\overline{Q}$), $\overline{Q}$ = High		100	350	600	mV
V_{ICM}	Input Common-Mode Voltage		0.3	1.2	2.2	V

Extended LVDS DC Specifications (LVDSEXT_25)

Table 10: **Extended LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.785	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.715	–	–	V
V_{ODIFF}	Differential Output Voltage (Q – $\overline{Q}$), Q = High (Q – $\overline{Q}$), $\overline{Q}$ = High for XC devices	R_T = 100 Ω across Q and $\overline{Q}$ signals	350	–	840	mV
	Differential Output Voltage (Q – $\overline{Q}$), Q = High (Q – $\overline{Q}$), $\overline{Q}$ = High for XQ devices		350	–	850	mV
V_{OCM}	Output Common-Mode Voltage for XC devices	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.075	1.250	1.425	V
	Output Common-Mode Voltage for XQ devices		1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q – $\overline{Q}$), Q = High (Q – $\overline{Q}$), $\overline{Q}$ = High	Common-mode input voltage = 1.25V	100	–	1000	mV
V_{ICM}	Input Common-Mode Voltage	Differential input voltage = ±350 mV	0.3	1.2	2.2	V

GTX Transceiver Specifications

GTX Transceiver DC Characteristics

Table 13: **Absolute Maximum Ratings for GTX Transceivers(1)**

Symbol	Description	Min	Max	Units
MGTAVCC	Analog supply voltage for the GTX transmitter and receiver circuits relative to GND	–0.5	1.1	V
MGTAVTT	Analog supply voltage for the GTX transmitter and receiver termination circuits relative to GND	–0.5	1.32	V
MGTAVTTRCAL	Analog supply voltage for the resistor calibration circuit of the GTX transceiver column	–0.5	1.32	V
V_{IN}	Receiver (RXP/RXN) and Transmitter (TXP/TXN) absolute input voltage	–0.5	1.32	V
$V_{MGTREFCLK}$	Reference clock absolute input voltage	–0.5	1.32	V

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.

Table 14: **Recommended Operating Conditions for GTX Transceivers(1)(2)**

Symbol	Description	Speed Grade	PLL Frequency	Min	Typ	Max	Units
MGTAVCC	Analog supply voltage for the GTX transmitter and receiver circuits relative to GND	-3, -2(3)	> 2.7 GHz	1.0	1.03	1.06	V
		-3, -2(3)	≤ 2.7 GHz	0.95	1.0	1.06	V
		-1	≤ 2.7 GHz	0.95	1.0	1.06	V
		-1L	≤ 2.7 GHz	0.95	1.0	1.05	V
MGTAVTT	Analog supply voltage for the GTX transmitter and receiver termination circuits relative to GND	All	–	1.14	1.2	1.26	V
MGTAVTTRCAL	Analog supply voltage for the resistor calibration circuit of the GTX transceiver column	All	–	1.14	1.2	1.26	V

Notes:

1. Each voltage listed requires the filter circuit described in UG366: *Virtex-6 FPGA GTX Transceivers User Guide*.
2. Voltages are specified for the temperature range of T_j = –40°C to +100°C for all XC devices and T_j = –55°C to +125°C for the XQ devices
3. If a GTX Quad contains transceivers operating with a mixture of PLL frequencies above and below 2.7 GHz, the MGTAVCC voltage supply must be in the range of 1.0V to 1.06V.

Table 15: **GTX Transceiver Supply Current (per Lane) (1)(2)**

Symbol	Description	Typ	Max	Units
$I_{MGTAVTT}$	MGTAVTT supply current for one GTX transceiver	55.9	Note 2	mA
$I_{MGTAVCC}$	MGTAVCC supply current for one GTX transceiver	56.1		mA
$MGTR_{REF}$	Precision reference resistor for internal calibration termination	100.0 ± 1% tolerance		Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C, with a 3.125 Gb/s line rate.
2. Values for currents of other transceiver configurations and conditions can be obtained by using the XPower Estimator (XPE) or XPower Analyzer (XPA) tools.

Table 23: **GTX Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTXTX}	Serial data rate range		0.480	–	F_{GTXMAX}	Gb/s
T_{RTX}	TX Rise time	20%–80%	–	120	–	ps
T_{FTX}	TX Fall time	80%–20%	–	120	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	350	ps
$V_{TXOOBVDPP}$	Electrical idle amplitude		–	–	15	mV
$T_{TXOOBTRANSITION}$	Electrical idle transition time		–	–	75	ns
$TJ_{6.5}$	Total Jitter(2)(3)	6.5 Gb/s	–	–	0.33	UI
$DJ_{6.5}$	Deterministic Jitter(2)(3)		–	–	0.17	UI
$TJ_{5.0}$	Total Jitter(2)(3)	5.0 Gb/s	–	–	0.33	UI
$DJ_{5.0}$	Deterministic Jitter(2)(3)		–	–	0.15	UI
$TJ_{4.25}$	Total Jitter(2)(3)	4.25 Gb/s	–	–	0.33	UI
$DJ_{4.25}$	Deterministic Jitter(2)(3)		–	–	0.14	UI
$TJ_{3.75}$	Total Jitter(2)(3)	3.75 Gb/s	–	–	0.34	UI
$DJ_{3.75}$	Deterministic Jitter(2)(3)		–	–	0.16	UI
$TJ_{3.125}$	Total Jitter(2)(3)	3.125 Gb/s	–	–	0.2	UI
$DJ_{3.125}$	Deterministic Jitter(2)(3)		–	–	0.1	UI
$TJ_{3.125L}$	Total Jitter(2)(3)	3.125 Gb/s(4)	–	–	0.35	UI
$DJ_{3.125L}$	Deterministic Jitter(2)(3)		–	–	0.16	UI
$TJ_{2.5}$	Total Jitter(2)(3)	2.5 Gb/s(5)	–	–	0.20	UI
$DJ_{2.5}$	Deterministic Jitter(2)(3)		–	–	0.08	UI
$TJ_{1.25}$	Total Jitter(2)(3)	1.25 Gb/s(6)	–	–	0.15	UI
$DJ_{1.25}$	Deterministic Jitter(2)(3)		–	–	0.06	UI
TJ_{600}	Total Jitter(2)(3)	600 Mb/s	–	–	0.1	UI
DJ_{600}	Deterministic Jitter(2)(3)		–	–	0.03	UI
TJ_{480}	Total Jitter(2)(3)	480 Mb/s	–	–	0.1	UI
DJ_{480}	Deterministic Jitter(2)(3)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TXENPMAPHASEALIGN enabled for up to 12 consecutive transmitters (three fully populated GTX Quads).
2. Using PLL_DIVSEL_FB = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. All jitter values are based on a bit-error ratio of $1e^{-12}$.
4. PLL frequency at 1.5625 GHz and OUTDIV = 1.
5. PLL frequency at 2.5 GHz and OUTDIV = 2.
6. PLL frequency at 2.5 GHz and OUTDIV = 4.

Table 24: **GTX Transceiver Receiver Switching Characteristics**

Symbol	Description		Min	Typ	Max	Units
F_{GTXRX}	Serial data rate	RX oversampler not enabled	0.600	–	F_{GTXMAX}	Gb/s
		RX oversampler enabled	0.480	–	0.600	Gb/s
$T_{RXELECIDLE}$	Time for RXELECIDLE to respond to loss or restoration of data		–	75	–	ns
$RX_{OOBVDPP}$	OOB detect threshold peak-to-peak		60	–	150	mV
RX_{SST}	Receiver spread-spectrum tracking(1)	Modulated @ 33 KHz	–5000	–	0	ppm
RX_{RL}	Run length (CID)	Internal AC capacitor bypassed	–	–	512	UI
RX_{PPMTOL}	Data/REFCLK PPM offset tolerance	CDR 2nd-order loop disabled	–200	–	200	ppm
		CDR 2nd-order loop enabled	–2000	–	2000	ppm
SJ Jitter Tolerance(2)						
$JT\_SJ_{6.5}$	Sinusoidal Jitter(3)	6.5 Gb/s	0.44	–	–	UI
$JT\_SJ_{5.0}$	Sinusoidal Jitter(3)	5.0 Gb/s	0.44	–	–	UI
$JT\_SJ_{4.25}$	Sinusoidal Jitter(3)	4.25 Gb/s	0.44	–	–	UI
$JT\_SJ_{3.75}$	Sinusoidal Jitter(3)	3.75 Gb/s	0.44	–	–	UI
$JT\_SJ_{3.125}$	Sinusoidal Jitter(3)	3.125 Gb/s	0.45	–	–	UI
$JT\_SJ_{3.125L}$	Sinusoidal Jitter(3)	3.125 Gb/s(4)	0.45	–	–	UI
$JT\_SJ_{2.5}$	Sinusoidal Jitter(3)	2.5 Gb/s(5)	0.5	–	–	UI
$JT\_SJ_{1.25}$	Sinusoidal Jitter(3)	1.25 Gb/s(6)	0.5	–	–	UI
JT_SJ_{600}	Sinusoidal Jitter(3)	600 Mb/s	0.4	–	–	UI
JT_SJ_{480}	Sinusoidal Jitter(3)	480 Mb/s	0.4	–	–	UI
SJ Jitter Tolerance with Stressed Eye(2)						
$JT\_TJSE_{3.125}$	Total Jitter with Stressed Eye(7)	3.125 Gb/s	0.70	–	–	UI
		5.0 Gb/s	0.70	–	–	UI
$JT\_SJSE_{3.125}$	Sinusoidal Jitter with Stressed Eye(7)	3.125 Gb/s	0.1	–	–	UI
		5.0 Gb/s	0.1	–	–	UI

Notes:

1. Using PLL_RXDIVSEL_OUT = 1, 2, and 4.
2. All jitter values are based on a bit error ratio of $1e^{-12}$.
3. The frequency of the injected sinusoidal jitter is 80 MHz.
4. PLL frequency at 1.5625 GHz and OUTDIV = 1.
5. PLL frequency at 2.5 GHz and OUTDIV = 2.
6. PLL frequency at 2.5 GHz and OUTDIV = 4.
7. Composite jitter with RX equalizer enabled. DFE disabled.

Figure 4 shows the timing parameters in Table 27.

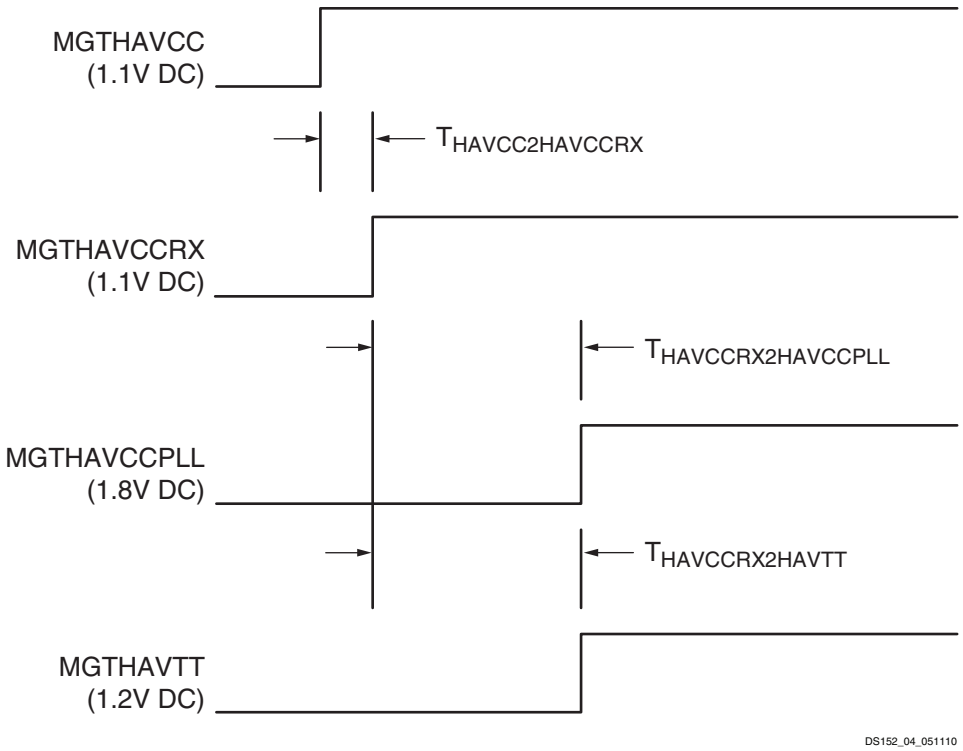

Figure 4: **GTH Transceiver Power Supply Power-On Sequencing**

Table 28: **GTH Transceiver Supply Current**

Symbol	Description	Typ(1)	Max	Units
$I_{MGTHAVCC}$	MGTHAVCC supply current for one GTH Quad (4 lanes)	571	Note 2	mA
$I_{MGTHAVCCRX}$	MGTHAVCCRX supply current for a GTH Quad (4 lanes)	254	Note 2	mA
$I_{MGTHAVTT}$	MGTHAVTT supply current for one GTH Quad (4 lanes)	93	Note 2	mA
$I_{MGTHAVCCPLL}$	MGTHAVCCPLL supply current for one GTH Quad (4 lanes)	219	Note 2	mA
$MGTR_{REF}$	Precision reference resistor for internal calibration termination	1000.0 ± 1% tolerance		Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C, with a 10.3125 Gb/s line rate.
2. Values for currents other than the values specified in this table can be obtained by using the XPower Estimator (XPE) or XPower Analyzer (XPA) tools.

Table 29: **GTH Transceiver Quiescent Supply Current(1)(2)**

Symbol	Description	Typ(3)	Max	Units
$I_{MGTHAVCCQ}$	Quiescent MGTHAVCC Supply Current for one GTH Quad (4 lanes)	65	Note 4	mA
$I_{MGTHAVCCRXQ}$	Quiescent MGTHAVCCRX Supply Current for one GTH Quad (4 lanes)	17	Note 4	mA
$I_{MGTHAVTTQ}$	Quiescent MGTHAVTT Supply Current for one GTH Quad (4 lanes)	1	Note 4	mA
$I_{MGTHAVCCPLLQ}$	Quiescent MGTHAVCCPLL Supply Current for one GTH Quad (4 lanes)	1	Note 4	mA

Notes:

1. Device powered and unconfigured.
2. GTH transceiver quiescent supply current for an entire device can be calculated by multiplying the values in this table by the number of available GTH transceivers.
3. Typical values are specified at nominal voltage, 25°C.
4. Currents for conditions other than values specified in this table can be obtained by using the XPE or XPA tools.

Table 35: **GTH Transceiver User Clock Switching Characteristics (1)**

Symbol	Description	Conditions	Speed Grade			Units
			-3	-2	-1	
F_{TXOUT}	TXUSERCLKOUT maximum frequency		350	350	323	MHz
F_{RXOUT}	RXUSERCLKOUT maximum frequency		350	350	323	MHz
F_{TXIN}	TXUSERCLKIN maximum frequency	16-bit data path	350	350	323	MHz
		20-bit data path	280	280	258	MHz
		32-bit data path	350	350	323	MHz
		40-bit data path	280	280	258	MHz
		64-bit data path	175	175	162	MHz
		80-bit data path	140	140	129	MHz
		64B/66B-bit data path	170	170	157	MHz
F_{RXIN}	RXUSERCLKIN maximum frequency	16-bit data path	350	350	323	MHz
		20-bit data path	280	280	258	MHz
		32-bit data path	350	350	323	MHz
		40-bit data path	280	280	258	MHz
		64-bit data path	175	175	162	MHz
		80-bit data path	140	140	129	MHz
		64B/66B-bit data path	170	170	157	MHz

Notes:

1. Clocking must be implemented as described in UG371:*Virtex-6 FPGA GTH Transceivers User Guide*.

Table 36: **GTH Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
T_{RTX}	TX Rise time	20%–80%	–	50(3)	–	ps
T_{FTX}	TX Fall time	80%–20%	–	50(3)	–	ps
T_{LLSKEW}	TX lane-to-lane skew	within one GTH Quad	–	–	300	ps
Transmitter Output Jitter(1)(2)						
$TJ_{11.18}$	Total Jitter	11.181 Gb/s	–	–	0.280	UI
$DJ_{11.18}$	Deterministic Jitter		–	–	0.170	UI
$TJ_{10.3125}$	Total Jitter	10.3125 Gb/s	–	–	0.280	UI
$DJ_{10.3125}$	Deterministic Jitter		–	–	0.170	UI
$TJ_{9.953}$	Total Jitter	9.953 Gb/s	–	–	0.280	UI
$DJ_{9.953}$	Deterministic Jitter		–	–	0.170	UI
$TJ_{2.667}$	Total Jitter	2.667 Gb/s	–	–	0.110	UI
$DJ_{2.667}$	Deterministic Jitter		–	–	0.060	UI
$TJ_{2.488}$	Total Jitter	2.488 Gb/s	–	–	0.110	UI
$DJ_{2.488}$	Deterministic Jitter		–	–	0.060	UI

Notes:

1. These values are NOT intended for protocol specific compliance determinations.
2. All jitter values are based on a bit-error ratio of $1e^{-12}$.
3. Rise and fall times are specified at the transmitter package balls.

Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Virtex-6 devices. The numbers reported here are worst-case values; they have all been fully characterized. These values are subject to the same guidelines as the Switching Characteristics, page 26.

Table 41: **Interface Performances**

Description	Speed Grade			
	-3	-2	-1	-1L
Networking Applications				
SDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 8)	710 Mb/s	710 Mb/s	650 Mb/s	585 Mb/s
DDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 10)	1.4 Gb/s	1.3 Gb/s	1.25 Gb/s	1.1 Gb/s
SDR LVDS receiver (SFI-4.1)(1)	710 Mb/s	710 Mb/s	650 Mb/s	585 Mb/s
DDR LVDS receiver (SPI-4.2)(1)	1.4 Gb/s	1.3 Gb/s	1.1 Gb/s	0.9 Gb/s
Maximum Physical Interface (PHY) Rate for Memory Interfaces(2)(3)(4)				
DDR2	800 Mb/s	800 Mb/s	800 Mb/s	606 Mb/s
DDR3	1066 Mb/s	1066 Mb/s	800 Mb/s	800 Mb/s
QDR II + SRAM	400 MHz	350 MHz	300 MHz	–
RLDRAM II	500 MHz	400 MHz	350 MHz	–

Notes:

1. LVDS receivers are typically bounded with certain applications where specific DPA algorithms dominate deterministic performance.
2. Verified on Xilinx memory characterization platforms designed according to the guidelines in UG: *Virtex-6 FPGA Memory Interface Solutions User Guide*.
3. Consult DS186: *Virtex-6 FPGA Memory Interface Solutions Data Sheet* for performance and feature information on memory interface cores (controller plus PHY).
4. Memory Interface data rates have not been tested over the junction temperature operating range for military (M) temperature devices. Customers are responsible for specifying and testing their specific M temperature grade memory implementation.

IOB Pad Input/Output/3-State Switching Characteristics

Table 44 (for commercial (XC) Virtex-6 devices) and Table 45 (for the Defense-grade (XQ) Virtex-6 devices) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.

T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.

T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer.

Table 46 summarizes the value of T_{IOTPHZ}. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state).

Table 44: **IOB Switching Characteristics for the Commercial (XC) Virtex-6 Devices**

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-2	-1	-1L	-3	-2	-1	-1L	-3	-2	-1	-1L	
LVDS_25	0.85	0.94	1.09	1.08	1.45	1.54	1.68	1.62	1.45	1.54	1.68	1.62	ns
LVDSEXT_25	0.85	0.94	1.09	1.08	1.53	1.65	1.84	1.73	1.53	1.65	1.84	1.73	ns
HT_25	0.85	0.94	1.09	1.08	1.51	1.62	1.78	1.69	1.51	1.62	1.78	1.69	ns
BLVDS_25	0.85	0.94	1.09	1.08	1.39	1.50	1.67	1.65	1.39	1.50	1.67	1.65	ns
RSDS_25 (point to point)	0.85	0.94	1.09	1.08	1.45	1.54	1.68	1.62	1.45	1.54	1.68	1.62	ns
HSTL_I	0.81	0.91	1.06	1.06	1.45	1.56	1.73	1.71	1.45	1.56	1.73	1.71	ns
HSTL_II	0.81	0.91	1.06	1.06	1.44	1.56	1.74	1.72	1.44	1.56	1.74	1.72	ns
HSTL_III	0.81	0.91	1.06	1.06	1.42	1.54	1.71	1.69	1.42	1.54	1.71	1.69	ns
HSTL_I_18	0.81	0.91	1.06	1.06	1.47	1.58	1.75	1.72	1.47	1.58	1.75	1.72	ns
HSTL_II_18	0.81	0.91	1.06	1.06	1.50	1.62	1.81	1.78	1.50	1.62	1.81	1.78	ns
HSTL_III_18	0.81	0.91	1.06	1.06	1.42	1.54	1.71	1.69	1.42	1.54	1.71	1.69	ns
SSTL2_I	0.81	0.91	1.06	1.06	1.49	1.60	1.77	1.74	1.49	1.60	1.77	1.74	ns
SSTL2_II	0.81	0.91	1.06	1.06	1.42	1.54	1.72	1.71	1.42	1.54	1.72	1.71	ns
SSTL15	0.81	0.91	1.06	1.06	1.42	1.54	1.71	1.69	1.42	1.54	1.71	1.69	ns
LVCMOS25, Slow, 2 mA	0.51	0.57	0.66	0.70	5.09	5.46	6.01	5.63	5.09	5.46	6.01	5.63	ns
LVCMOS25, Slow, 4 mA	0.51	0.57	0.66	0.70	3.30	3.49	3.79	3.65	3.30	3.49	3.79	3.65	ns
LVCMOS25, Slow, 6 mA	0.51	0.57	0.66	0.70	2.62	2.81	3.08	2.95	2.62	2.81	3.08	2.95	ns
LVCMOS25, Slow, 8 mA	0.51	0.57	0.66	0.70	2.21	2.41	2.72	2.59	2.21	2.41	2.72	2.59	ns
LVCMOS25, Slow, 12 mA	0.51	0.57	0.66	0.70	1.80	1.95	2.17	2.10	1.80	1.95	2.17	2.10	ns
LVCMOS25, Slow, 16 mA	0.51	0.57	0.66	0.70	1.89	2.05	2.29	2.21	1.89	2.05	2.29	2.21	ns
LVCMOS25, Slow, 24 mA	0.51	0.57	0.66	0.70	1.68	1.82	2.02	1.98	1.68	1.82	2.02	1.98	ns
LVCMOS25, Fast, 2 mA	0.51	0.57	0.66	0.70	5.12	5.49	6.04	5.62	5.12	5.49	6.04	5.62	ns
LVCMOS25, Fast, 4 mA	0.51	0.57	0.66	0.70	3.28	3.50	3.82	3.65	3.28	3.50	3.82	3.65	ns
LVCMOS25, Fast, 6 mA	0.51	0.57	0.66	0.70	2.56	2.73	2.99	2.88	2.56	2.73	2.99	2.88	ns
LVCMOS25, Fast, 8 mA	0.51	0.57	0.66	0.70	2.11	2.33	2.65	2.53	2.11	2.33	2.65	2.53	ns
LVCMOS25, Fast, 12 mA	0.51	0.57	0.66	0.70	1.74	1.88	2.08	2.03	1.74	1.88	2.08	2.03	ns
LVCMOS25, Fast, 16 mA	0.51	0.57	0.66	0.70	1.77	1.92	2.13	2.08	1.77	1.92	2.13	2.08	ns

Table 44: **IOB Switching Characteristics for the Commercial (XC) Virtex-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-2	-1	-1L	-3	-2	-1	-1L	-3	-2	-1	-1L	
DIFF_SSTL18_I	0.85	0.94	1.09	1.08	1.47	1.58	1.75	1.73	1.47	1.58	1.75	1.73	ns
DIFF_SSTL18_I_DCI	0.85	0.94	1.09	1.08	1.40	1.51	1.67	1.65	1.40	1.51	1.67	1.65	ns
DIFF_SSTL18_II	0.85	0.94	1.09	1.08	1.39	1.50	1.67	1.66	1.39	1.50	1.67	1.66	ns
DIFF_SSTL18_II_DCI	0.85	0.94	1.09	1.08	1.36	1.47	1.63	1.62	1.36	1.47	1.63	1.62	ns
DIFF_SSTL18_II_T_DCI	0.85	0.94	1.09	1.08	1.40	1.51	1.67	1.65	1.40	1.51	1.67	1.65	ns
DIFF_SSTL15	0.81	0.91	1.06	1.06	1.42	1.54	1.71	1.69	1.42	1.54	1.71	1.69	ns
DIFF_SSTL15_DCI	0.81	0.91	1.06	1.06	1.41	1.52	1.68	1.66	1.41	1.52	1.68	1.66	ns
DIFF_SSTL15_T_DCI	0.81	0.91	1.06	1.06	1.41	1.52	1.68	1.66	1.41	1.52	1.68	1.66	ns

Table 45: **IOB Switching Characteristics for the Defense-grade (XQ) Virtex-6 Devices**

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
LVDS_25	0.94	1.09	1.08	1.54	2.16	1.62	1.54	2.16	1.62	ns
LVDSEXT_25	0.94	1.09	1.08	1.65	2.20	1.73	1.65	2.20	1.73	ns
HT_25	0.94	1.09	1.08	1.62	2.20	1.69	1.62	2.20	1.69	ns
BLVDS_25	0.94	1.09	1.08	1.50	3.18	1.65	1.50	3.18	1.65	ns
RSDS_25 (point to point)	0.94	1.09	1.08	1.54	2.22	1.62	1.54	2.22	1.62	ns
HSTL_I	0.91	1.06	1.06	1.56	2.44	1.71	1.56	2.44	1.71	ns
HSTL_II	0.91	1.06	1.06	1.56	2.21	1.72	1.56	2.21	1.72	ns
HSTL_III	0.91	1.06	1.06	1.54	2.50	1.69	1.54	2.50	1.69	ns
HSTL_I_18	0.91	1.06	1.06	1.58	2.43	1.72	1.58	2.43	1.72	ns
HSTL_II_18	0.91	1.06	1.06	1.62	2.30	1.78	1.62	2.30	1.78	ns
HSTL_III_18	0.91	1.06	1.06	1.54	2.49	1.69	1.54	2.49	1.69	ns
SSTL2_I	0.91	1.06	1.06	1.60	2.50	1.74	1.60	2.50	1.74	ns
SSTL2_II	0.91	1.06	1.06	1.54	2.49	1.71	1.54	2.49	1.71	ns
SSTL15	0.91	1.06	1.06	1.54	2.07	1.69	1.54	2.07	1.69	ns
LVCMOS25, Slow, 2 mA	0.57	0.66	0.70	5.46	6.01	5.63	5.46	6.01	5.63	ns
LVCMOS25, Slow, 4 mA	0.57	0.66	0.70	3.49	3.79	3.65	3.49	3.79	3.65	ns
LVCMOS25, Slow, 6 mA	0.57	0.66	0.70	2.81	3.08	2.95	2.81	3.08	2.95	ns
LVCMOS25, Slow, 8 mA	0.57	0.66	0.70	2.41	2.72	2.59	2.41	2.72	2.59	ns
LVCMOS25, Slow, 12 mA	0.57	0.66	0.70	1.95	2.23	2.10	1.95	2.23	2.10	ns
LVCMOS25, Slow, 16 mA	0.57	0.66	0.70	2.05	2.29	2.21	2.05	2.29	2.21	ns
LVCMOS25, Slow, 24 mA	0.57	0.66	0.70	1.82	2.24	1.98	1.82	2.24	1.98	ns
LVCMOS25, Fast, 2 mA	0.57	0.66	0.70	5.49	6.04	5.62	5.49	6.04	5.62	ns
LVCMOS25, Fast, 4 mA	0.57	0.66	0.70	3.50	3.82	3.65	3.50	3.82	3.65	ns
LVCMOS25, Fast, 6 mA	0.57	0.66	0.70	2.73	2.99	2.88	2.73	2.99	2.88	ns
LVCMOS25, Fast, 8 mA	0.57	0.66	0.70	2.33	2.65	2.53	2.33	2.65	2.53	ns
LVCMOS25, Fast, 12 mA	0.57	0.66	0.70	1.88	2.08	2.03	1.88	2.08	2.03	ns

Table 45: **IOB Switching Characteristics for the Defense-grade (XQ) Virtex-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
LVDCI_DV2_18	0.61	0.72	0.73	1.81	2.36	1.98	1.81	2.36	1.98	ns
LVDCI_DV2_15	0.73	0.85	0.85	1.77	2.30	1.98	1.77	2.30	1.98	ns
LVPECL_25	0.94	1.09	1.08	1.49	2.68	1.64	1.49	2.68	1.64	ns
HSTL_I_12	0.91	1.06	1.06	1.60	2.48	1.74	1.60	2.48	1.74	ns
HSTL_I_DCI	0.91	1.06	1.06	1.50	2.43	1.64	1.50	2.43	1.64	ns
HSTL_II_DCI	0.91	1.06	1.06	1.49	2.39	1.66	1.49	2.39	1.66	ns
HSTL_II_T_DCI	0.91	1.06	1.06	1.50	2.43	1.64	1.50	2.43	1.64	ns
HSTL_III_DCI	0.91	1.06	1.06	1.45	2.48	1.61	1.45	2.48	1.61	ns
HSTL_I_DCI_18	0.91	1.06	1.06	1.53	2.44	1.66	1.53	2.44	1.66	ns
HSTL_II_DCI_18	0.91	1.06	1.06	1.46	2.41	1.59	1.46	2.41	1.59	ns
HSTL_II _T_DCI_18	0.91	1.06	1.06	1.53	2.43	1.66	1.53	2.43	1.66	ns
HSTL_III_DCI_18	0.91	1.06	1.06	1.54	2.50	1.67	1.54	2.50	1.67	ns
DIFF_HSTL_I_18	0.94	1.09	1.08	1.58	2.30	1.72	1.58	2.30	1.72	ns
DIFF_HSTL_I_DCI_18	0.94	1.09	1.08	1.53	2.21	1.66	1.53	2.21	1.66	ns
DIFF_HSTL_I	0.94	1.09	1.08	1.56	2.28	1.71	1.56	2.28	1.71	ns
DIFF_HSTL_I_DCI	0.94	1.09	1.08	1.50	2.28	1.64	1.50	2.28	1.64	ns
DIFF_HSTL_II_18	0.94	1.09	1.08	1.62	2.33	1.78	1.62	2.33	1.78	ns
DIFF_HSTL_II_DCI_18	0.94	1.09	1.08	1.46	2.18	1.59	1.46	2.18	1.59	ns
DIFF_HSTL_II _T_DCI_18	0.94	1.09	1.08	1.53	2.22	1.66	1.53	2.22	1.66	ns
DIFF_HSTL_II	0.94	1.09	1.08	1.56	2.29	1.72	1.56	2.29	1.72	ns
DIFF_HSTL_II_DCI	0.94	1.09	1.08	1.49	2.26	1.66	1.49	2.26	1.66	ns
SSTL2_I_DCI	0.91	1.06	1.06	1.53	2.51	1.68	1.53	2.51	1.68	ns
SSTL2_II_DCI	0.91	1.06	1.06	1.50	2.50	1.69	1.50	2.50	1.69	ns
SSTL2_II_T_DCI	0.91	1.06	1.06	1.53	2.52	1.68	1.53	2.52	1.68	ns
SSTL18_I	0.91	1.06	1.06	1.58	2.48	1.73	1.58	2.48	1.73	ns
SSTL18_II	0.91	1.06	1.06	1.50	2.46	1.66	1.50	2.46	1.66	ns
SSTL18_I_DCI	0.91	1.06	1.06	1.51	2.49	1.65	1.51	2.49	1.65	ns
SSTL18_II_DCI	0.91	1.06	1.06	1.47	2.41	1.62	1.47	2.41	1.62	ns
SSTL18_II_T_DCI	0.91	1.06	1.06	1.51	2.49	1.65	1.51	2.49	1.65	ns
SSTL15_T_DCI	0.91	1.06	1.06	1.52	2.48	1.66	1.52	2.48	1.66	ns
SSTL15_DCI	0.91	1.06	1.06	1.52	2.48	1.66	1.52	2.48	1.66	ns
DIFF_SSTL2_I	0.94	1.09	1.08	1.60	2.34	1.74	1.60	2.34	1.74	ns
DIFF_SSTL2_I_DCI	0.94	1.09	1.08	1.53	2.25	1.68	1.53	2.25	1.68	ns
DIFF_SSTL2_II	0.94	1.09	1.08	1.54	2.29	1.71	1.54	2.29	1.71	ns
DIFF_SSTL2_II_DCI	0.94	1.09	1.08	1.50	2.23	1.69	1.50	2.23	1.69	ns
DIFF_SSTL2_II_T_DCI	0.94	1.09	1.08	1.53	2.26	1.68	1.53	2.26	1.68	ns
DIFF_SSTL18_I	0.94	1.09	1.08	1.58	2.22	1.73	1.58	2.22	1.73	ns
DIFF_SSTL18_I_DCI	0.94	1.09	1.08	1.51	2.30	1.65	1.51	2.30	1.65	ns

Table 48: **Output Delay Measurement Methodology *(Cont'd)***

Description	I/O Standard Attribute	R_{REF} (Ω)	C_{REF}[1] (pF)	V_{MEAS} (V)	V_{REF} (V)
HT (HyperTransport), 2.5V	LDT_25	100	0	0[2]	0.6
LVPECL (Low-Voltage Positive Emitter-Coupled Logic), 2.5V	LVPECL_25	100	0	0[2]	0
LVDCI/HSLVDCI, 2.5V	LVDCI_25, HSLVDCI_25	1M	0	1.25	0
LVDCI/HSLVDCI, 1.8V	LVDCI_18, HSLVDCI_18	1M	0	0.9	0
LVDCI/HSLVDCI, 1.5V	LVDCI_15, HSLVDCI_15	1M	0	0.75	0
HSTL (High-Speed Transceiver Logic), Class I & II, with DCI	HSTL_I_DCI, HSTL_II_DCI	50	0	V_{REF}	0.75
HSTL, Class III, with DCI	HSTL_III_DCI	50	0	0.9	1.5
HSTL, Class I & II, 1.8V, with DCI	HSTL_I_DCI_18, HSTL_II_DCI_18	50	0	V_{REF}	0.9
HSTL, Class III, 1.8V, with DCI	HSTL_III_DCI_18	50	0	1.1	1.8
SSTL (Stub Series Termi.Logic), Class I & II, 1.8V, with DCI	SSTL18_I_DCI, SSTL18_II_DCI	50	0	V_{REF}	0.9
SSTL, Class I & II, 2.5V, with DCI	SSTL2_I_DCI, SSTL2_II_DCI	50	0	V_{REF}	1.25

Notes:

1. C_{REF} is the capacitance of the probe, nominally 0 pF.
2. The value given is the differential output voltage.

Input/Output Logic Switching Characteristics

Table 49: **ILOGIC Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
Setup/Hold						
T_{ICE1CK}/T_{ICKCE1}	CE1 pin Setup/Hold with respect to CLK	0.21/ 0.03	0.25/ 0.04	0.27/ 0.04	0.31/ 0.05	ns
T_{ISRCK}/T_{ICKSR}	SR pin Setup/Hold with respect to CLK	0.66/ –0.08	0.78/ –0.08	0.96/ –0.08	1.09/ –0.11	ns
T_{IDOCK}/T_{IOCKD}	D pin Setup/Hold with respect to CLK without Delay	0.07/ 0.41	0.08/ 0.46	0.10/ 0.54	0.11/ 0.64	ns
T_{IDOCKD}/T_{IOCKDD}	DDLY pin Setup/Hold with respect to CLK (using IODELAY)	0.10/ 0.32	0.12/ 0.36	0.14/ 0.42	0.16/ 0.50	ns
Combinatorial						
T_{IDI}	D pin to O pin propagation delay, no Delay	0.15	0.17	0.20	0.23	ns
T_{IDID}	DDLY pin to O pin propagation delay (using IODELAY)	0.19	0.22	0.25	0.28	ns
Sequential Delays						
T_{IDLO}	D pin to Q1 pin using flip-flop as a latch without Delay	0.48	0.54	0.64	0.73	ns
T_{IDLOD}	DDLY pin to Q1 pin using flip-flop as a latch (using IODELAY)	0.52	0.58	0.68	0.78	ns
T_{ICKQ}	CLK to Q outputs	0.54	0.61	0.70	0.93	ns
T_{RQ_ILOGIC}	SR pin to OQ/TQ out	0.85	0.97	1.15	1.32	ns
T_{GSRQ_ILOGIC}	Global Set/Reset to Q outputs	7.60	7.60	10.51	10.51	ns
Set/Reset						
T_{RPW_ILOGIC}	Minimum Pulse Width, SR inputs	0.78	0.95	1.20	1.30	ns, Min

Input Serializer/Deserializer Switching Characteristics

Table 51: **ISERDES Switching Characteristics**

Symbol	Description	Speed Grade					Units
		-3	-2	-1 (XC)	-1 (XQ)	-1L	
Setup/Hold for Control Lines							
$T_{ISCCK\_BITSLIP}$/ $T_{ISCKC\_BITSLIP}$	BITSLIP pin Setup/Hold with respect to CLKDIV	0.07/ 0.15	0.08/ 0.16	0.09/ 0.17	0.09/ 0.17	0.14/ 0.17	ns
T_{ISCCK_CE} / T_{ISCKC_CE}(2)	CE pin Setup/Hold with respect to CLK (for CE1)	0.20/ 0.03	0.25/ 0.04	0.27/ 0.04	0.27/ 0.04	0.31/ 0.05	ns
T_{ISCCK_CE2} / T_{ISCKC_CE2}(2)	CE pin Setup/Hold with respect to CLKDIV (for CE2)	0.01/ 0.27	0.01 0.29	0.01/ 0.31	0.01/ 0.31	–0.05/ 0.35	ns
Setup/Hold for Data Lines							
T_{ISDCK_D} /T_{ISCKD_D}	D pin Setup/Hold with respect to CLK	0.07/ 0.08	0.08/ 0.09	0.09/ 0.11	0.09/ 0.11	0.11/ 0.19	ns
T_{ISDCK_DDLY} /T_{ISCKD_DDLY}	DDLY pin Setup/Hold with respect to CLK (using IODELAY)(1)	0.10/ 0.05	0.12/ 0.06	0.14/ 0.07	0.14/ 0.07	0.16/ 0.15	ns
$T_{ISDCK\_D\_DDR}$ /$T_{ISCKD\_D\_DDR}$	D pin Setup/Hold with respect to CLK at DDR mode	0.07/ 0.08	0.08/ 0.09	0.09/ 0.11	0.09/ 0.11	0.11/ 0.19	ns
$T_{ISDCK\_DDLY\_DDR}$ $T_{ISCKD\_DDLY\_DDR}$	D pin Setup/Hold with respect to CLK at DDR mode (using IODELAY)(1)	0.10/ 0.05	0.12/ 0.06	0.14/ 0.07	0.14/ 0.07	0.16/ 0.15	ns
Sequential Delays							
T_{ISCKO_Q}	CLKDIV to out at Q pin	0.57	0.66	0.75	0.80	0.88	ns
Propagation Delays							
T_{ISDO_DO}	D input to DO output pin	0.19	0.22	0.25	0.25	0.28	ns

Notes:

1. Recorded at 0 tap value.
2. T_{ISCCK_CE2} and T_{ISCKC_CE2} are reported as T_{ISCCK_CE}/T_{ISCKC_CE} in TRACE report.

Input/Output Delay Switching Characteristics

Table 53: **Input/Output Delay Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
IDELAYCTRL						
T_{DLYCCO_RDY}	Reset to Ready for IDELAYCTRL	3.00	3.00	3.00	3.25	µs
$F_{IDELAYCTRL\_REF}$	REFCLK frequency = 200.0(1)	200	200	200	200	MHz
	REFCLK frequency = 300.0(1)	300	300	–	–	MHz
IDELAYCTRL_REF_PRECISION	REFCLK precision	±10	±10	±10	±10	MHz
$T_{IDELAYCTRL\_RPW}$	Minimum Reset pulse width	50.00	50.00	50.00	52.50	ns
IODELAY						
$T_{IDELAYRESOLUTION}$	IODELAY Chain Delay Resolution	$1/(32 \times 2 \times F_{REF})$				ps
$T_{IDELAYPAT\_JIT}$	Pattern dependent period jitter in delay chain for clock pattern.(2)	0	0	0	0	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23).(3)	±5	±5	±5	±5	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23).(4)	±9	±9	±9	±9	ps per tap
$T_{IODELAY\_CLK\_MAX}$	Maximum frequency of CLK input to IODELAY	500.00	420.00	300.00	300.00	MHz
T_{IODCCK_CE} / T_{IODCKC_CE}	CE pin Setup/Hold with respect to CK	0.45/ –0.09	0.53/ –0.09	0.65/ –0.09	0.84/ –0.14	ns
T_{IODCK_INC}/ T_{IODCKC_INC}	INC pin Setup/Hold with respect to CK	0.23/ –0.02	0.27/ –0.01	0.31/ 0.00	0.27/ –0.04	ns
T_{IODCCK_RST}/ T_{IODCKC_RST}	RST pin Setup/Hold with respect to CK	0.57/ –0.08	0.62/ –0.08	0.69/ –0.08	0.74/ –0.13	ns
T_{IODDO_T}	TSCONTROL delay to MUXE/MUXF switching and through IODELAY	Note 5	Note 5	Note 5	Note 5	ps
$T_{IODDO\_IDATAIN}$	Propagation delay through IODELAY	Note 5	Note 5	Note 5	Note 5	ps
$T_{IODDO\_ODATAIN}$	Propagation delay through IODELAY	Note 5	Note 5	Note 5	Note 5	ps

Notes:

1. Average Tap Delay at 200 MHz = 78 ps, at 300 MHz = 52 ps.
2. When HIGH_PERFORMANCE mode is set to TRUE or FALSE.
3. When HIGH_PERFORMANCE mode is set to TRUE
4. When HIGH_PERFORMANCE mode is set to FALSE.
5. Delay depends on IODELAY tap setting. See TRACE report for actual values.

CLB Switching Characteristics

Table 54: **CLB Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
Combinatorial Delays						
T_{ILO}	An – Dn LUT address to A	0.06	0.07	0.07	0.09	ns, Max
	An – Dn LUT address to AMUX/CMUX	0.18	0.20	0.22	0.25	ns, Max
	An – Dn LUT address to BMUX_A	0.28	0.31	0.36	0.40	ns, Max

Table 58: **DSP48E1 Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade					Units
		-3	-2	-1 (XC)	-1 (XQ)	-1L	
Maximum Frequency							
F_{MAX}	With all registers used	600	540	450	450	410	MHz
F_{MAX_PATDET}	With pattern detector	551	483	408	408	356	MHz
$F_{MAX\_MULT\_NOMREG}$	Two register multiply without MREG	356	311	262	262	224	MHz
$F_{MAX\_MULT\_NOMREG\_PATDET}$	Two register multiply without MREG with pattern detect	327	286	241	241	211	MHz
$F_{MAX\_PREADD\_MULT\_NOADREG}$	Without ADREG	398	347	292	292	254	MHz
$F_{MAX\_PREADD\_MULT\_NOADREG\_PATDET}$	Without ADREG with pattern detect	398	347	292	292	254	MHz
$F_{MAX\_NOPIPELINEREG}$	Without pipeline registers (MREG, ADREG)	266	233	196	196	171	MHz
$F_{MAX\_NOPIPELINEREG\_PATDET}$	Without pipeline registers (MREG, ADREG) with pattern detect	250	219	184	184	160	MHz

Configuration Switching Characteristics

Table 59: **Configuration Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
Power-up Timing Characteristics						
T_{PL}(1)	Program Latency	5	5	5	5	ms, Max
T_{POR}(1)	Power-on-Reset	15/55	15/55	15/55	15/60	ms, Min/Max
T_{ICCK}	CCLK (output) delay	400	400	400	400	ns, Min
$T_{PROGRAM}$	Program Pulse Width	250	250	250	250	ns, Min
Master/Slave Serial Mode Programming Switching						
T_{DCCK}/T_{CCKD}	DIN Setup/Hold, slave mode	4.0/0.0	4.0/0.0	4.0/0.0	4.5/0.0	ns, Min
T_{DSCCK}/T_{SCCKD}	DIN Setup/Hold, master mode	4.0/0.0	4.0/0.0	4.0/0.0	5.0/0.0	ns, Min
T_{CCO}	DOUT at 2.5V	6	6	6	7	ns, Max
	DOUT at 1.8V	6	6	6	7	ns, Max
F_{MCCK}	Maximum CCLK frequency, serial modes	105	105	105	70	MHz, Max
$F_{MCCKTOL}$	Frequency Tolerance, master mode with respect to nominal CCLK.	55	55	55	60	%
F_{MSCCK}	Slave mode external CCLK	100	100	100	100	MHz
SelectMAP Mode Programming Switching						
T_{SMDCCK}/T_{SMCCKD}	SelectMAP Data Setup/Hold	4.0/0.0	4.0/0.0	4.0/0.0	5.5/0.0	ns, Min
$T_{SMCSCCK}/T_{SMCCKCS}$	CSI_B Setup/Hold	4.0/0.0	4.0/0.0	4.0/0.0	5.5/0.0	ns, Min
T_{SMCCKW}/T_{SMWCCK}	RDWR_B Setup/Hold	10.0/0.0	10.0/0.0	10.0/0.0	16.0/0.0	ns, Min
$T_{SMCKCSO}$	CSO_B clock to out (330 Ω pull-up resistor required)	6	6	6	7	ns, Max
T_{SMCO}	CCLK to DATA out in readback at 2.5V	6	6	6	7	ns, Max
	CCLK to DATA out in readback at 1.8V	6	6	6	7	ns, Max

Table 59: **Configuration Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T_{SMCKBY}	CCLK to BUSY out in readback at 2.5V	6	6	6	7	ns, Max
	CCLK to BUSY out in readback at 1.8V	6	6	6	7	ns, Max
F_{SMCCK}	Maximum Frequency with respect to nominal CCLK	100	100	100	70	MHz, Max
F_{RBCCK}	Maximum Readback Frequency with respect to nominal CCLK	100	100	100	60	MHz, Max
$F_{MCCKTOL}$	Frequency tolerance, master mode with respect to nominal CCLK	55	55	55	60	%
Boundary-Scan Port Timing Specifications						
T_{TAPTCK}/T_{TCKTAP}	TMS and TDI Setup time before TCK/ Hold time after TCK	3.0/2.0	3.0/2.0	3.0/2.0	4.0/2.0	ns, Min
T_{TCKTDO}	TCK falling edge to TDO output valid at 2.5V	6	6	6	7	ns, Max
	TCK falling edge to TDO output valid at 1.8V	6	6	6	7	ns, Max
F_{TCK}	Maximum configuration TCK clock frequency	66	66	66	33	MHz, Max
F_{TCKB_MIN}	Minimum boundary-scan TCK clock frequency when using IEEE Std 1149.6 (AC-JTAG). Minimum operating temperature for IEEE Std 1149.6 is 0°C.	15	15	15	15	MHz, Min
F_{TCKB}	Maximum boundary-scan TCK clock frequency	66	66	66	33	MHz, Max
BPI Master Flash Mode Programming Switching						
T_{BPICCO}[(2)]	ADDR[25:0], RS[1:0], FCS_B, FOE_B, FWE_B outputs valid after CCLK rising edge at 2.5V	6	6	6	7	ns
	ADDR[25:0], RS[1:0], FCS_B, FOE_B, FWE_B outputs valid after CCLK rising edge at 1.8V	6	6	6	7	ns
T_{BPIDCC}/T_{BPICCD}	Setup/Hold on D[15:0] data input pins	4.0/0.0	4.0/0.0	4.0/0.0	5.0/0.0	ns
$T_{INITADDR}$	Minimum period of initial ADDR[25:0] address cycles	3	3	3	3	CCLK cycles
SPI Master Flash Mode Programming Switching						
$T_{SPIDCC}/T_{SPIDCCD}$	DIN Setup/Hold before/after the rising CCLK edge	3.0/0.0	3.0/0.0	3.0/0.0	3.5/0.0	ns
T_{SPICCM}	MOSI clock to out at 2.5V	6	6	6	7	ns
	MOSI clock to out at 1.8V	6	6	6	7	ns
$T_{SPICCFC}$	FCS_B clock to out at 2.5V	6	6	6	7	ns
	FCS_B clock to out at 1.8V	6	6	6	7	ns
$T_{FSINIT}/T_{FSINITH}$	FS[2:0] to INIT_B rising edge Setup and Hold	2	2	2	2	µs
CCLK Output (Master Modes)						
T_{MCCKL}	Master CCLK clock Low time duty cycle	45/55	45/55	45/55	40/60	%, Min/Max
T_{MCCKH}	Master CCLK clock High time duty cycle	45/55	45/55	45/55	40/60	%, Min/Max
CCLK Input (Slave Modes)						
T_{SCCKL}	Slave CCLK clock minimum Low time	2.5	2.5	2.5	2.5	ns, Min
T_{SCCKH}	Slave CCLK clock minimum High time	2.5	2.5	2.5	2.5	ns, Min
Dynamic Reconfiguration Port (DRP) for MMCM Before and After DCLK						
F_{DCK}	Maximum frequency for DCLK	200	200	200	200	MHz
$T_{MMCMDCK\_DADDR}$/ $T_{MMCMCKD\_DADDR}$	DADDR Setup/Hold	1.25/ 0.00	1.40/ 0.00	1.63/ 0.00	1.64/ 0.00	ns

Table 64: **MMCM Specification *(Cont'd)***

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
$RST_{MINPULSE}$	Minimum Reset Pulse Width	1.5	1.5	1.5	1.5	ns
F_{PFDMAX}	Maximum Frequency at the Phase Frequency Detector with Bandwidth Set to High or Optimized(9)	550	500	450	450	MHz
	Maximum Frequency at the Phase Frequency Detector with Bandwidth Set to Low	300	300	300	300	MHz
F_{PFDMIN}	Minimum Frequency at the Phase Frequency Detector with Bandwidth Set to High or Optimized	135	135	135	135	MHz
	Minimum Frequency at the Phase Frequency Detector with Bandwidth Set to Low	10	10	10	10	MHz
$T_{FBDELAY}$	Maximum Delay in the Feedback Path	3 ns Max or one CLKIN cycle				
$T_{MMCMDCK\_PSEN}$/ $T_{MMCMCKD\_PSEN}$	Setup and Hold of Phase Shift Enable	1.04 0.00	1.04 0.00	1.04 0.00	1.04 0.00	ns
$T_{MMCMDCK\_PSINCDEC}$/ $T_{MMCMCKD\_PSINCDEC}$	Setup and Hold of Phase Shift Increment/Decrement	1.04 0.00	1.04 0.00	1.04 0.00	1.04 0.00	ns
$T_{MMCMCKO\_PSDONE}$	Phase Shift Clock-to-Out of PSDONE	0.32	0.34	0.38	0.38	ns

Notes:

1. When DIVCLK_DIVIDE = 3 or 4, F_{INMAX} is 315 MHz.
2. This duty cycle specification does not apply to the GTH_QUAD (GTH) to MMCM connection. The GTH transceivers drive the MMCMs at the following maximum frequencies: 323 MHz for -1 speed grade devices, 350 MHz for -2 speed grade devices, or 350 MHz for -3 speed grade devices.
3. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
4. The static offset is measured between any MMCM outputs with identical phase.
5. Values for this parameter are available in the Clocking Wizard. See http://www.xilinx.com/products/intellectual-property/clocking_wizard.htm.
6. Includes global clock buffer.
7. Calculated as $F_{VCO}/128$ assuming output duty cycle is 50%.
8. When CASCADE4_OUT = TRUE, F_{OUTMIN} is 0.036 MHz.
9. In ISE software 12.3 (or earlier versions supporting the Virtex-6 family), the phase frequency detector Optimized bandwidth setting is equivalent to the High bandwidth setting. Starting with ISE software 12.4, the Optimized bandwidth setting is automatically adjusted to Low when the software can determine that the phase frequency detector input is less than 135 MHz.

Virtex-6 Device Pin-to-Pin Output Parameter Guidelines

All devices are 100% functionally tested. The representative values for typical pin locations and normal clock loading are listed in Table 65. Values are expressed in nanoseconds unless otherwise noted.

Table 65: **Global Clock Input to Output Delay Without MMCM**

Symbol	Description	Device	Speed Grade				Units
			-3	-2	-1	-1L	
LVCMOS25 Global Clock Input to Output Delay using Output Flip-Flop, 12mA, Fast Slew Rate, *without* MMCM.							
T_{ICKOF}	Global Clock input and OUTFF *without* MMCM	XC6VLX75T	4.91	5.32	5.88	6.02	ns
		XC6VLX130T	4.89	5.33	6.00	6.13	ns
		XC6VLX195T	5.02	5.46	6.13	6.27	ns
		XC6VLX240T	5.02	5.46	6.13	6.27	ns
		XC6VLX365T	5.30	5.75	6.43	6.37	ns
		XC6VLX550T	N/A	6.02	6.72	6.60	ns
		XC6VLX760	N/A	6.26	6.97	6.87	ns
		XC6VSX315T	5.40	5.85	6.54	6.49	ns
		XC6VSX475T	N/A	6.01	6.71	6.61	ns
		XC6VHX250T	5.18	5.63	6.30	N/A	ns
		XC6VHX255T	5.20	5.66	6.34	N/A	ns
		XC6VHX380T	5.38	5.84	6.53	N/A	ns
		XC6VHX565T	N/A	6.03	6.71	N/A	ns
		XQ6VLX130T	N/A	5.33	6.00	6.13	ns
		XQ6VLX240T	N/A	5.46	6.13	6.27	ns
		XQ6VLX550T	N/A	N/A	6.72	6.60	ns
		XQ6VSX315T	N/A	5.85	6.54	6.49	ns
		XQ6VSX475T	N/A	N/A	6.71	6.61	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.

Table 73: **Sample Window**

Symbol	Description	Device	Speed Grade				Units
			-3	-2	-1	-1L	
T_{SAMP}	Sampling Error at Receiver Pins(1)	All	510	560	610	670	ps
T_{SAMP_BUFIO}	Sampling Error at Receiver Pins using BUFIO(2)	All	300	350	400	440	ps

Notes:

1. This parameter indicates the total sampling error of Virtex-6 FPGA DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the MMCM to capture the DDR input registers' edges of operation. These measurements include:
   - CLK0 MMCM jitter
   - MMCM accuracy (phase offset)
   - MMCM phase shift resolution

   These measurements do not include package or clock tree skew.
2. This parameter indicates the total sampling error of Virtex-6 FPGA DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the BUFIO clock network and IODELAY to capture the DDR input registers' edges of operation. These measurements do not include package or clock tree skew.

Table 74: **Pin-to-Pin Setup/Hold and Clock-to-Out**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
Data Input Setup and Hold Times Relative to a Forwarded Clock Input Pin Using BUFIO						
T_{PSCS}/T_{PHCS}	Setup/Hold of I/O clock	–0.28/1.09	–0.28/1.16	–0.28/1.33	–0.18/1.79	ns
Pin-to-Pin Clock-to-Out Using BUFIO						
$T_{ICKOFCS}$	Clock-to-Out of I/O clock	4.22	4.59	5.22	5.63	ns

Revision History

The following table shows the revision history for this document:

Date	Version	Description of Revisions
06/24/09	1.0	Initial Xilinx release.
07/16/09	1.1	Revised the maximum V_{CCAUX} and V_{IN} numbers in Table 2, page 2. Removed empty column from Table 3, page 3. Revised specifications on Table 20, page 13. Updated Table 38, page 22 and added notes 1 and 2. Revised T_{DLYCCO_RDY}, $T_{IDELAYCTRL\_RPW}$, and $T_{IDELAYPAT\_JIT}$ in Table 53, page 41. Updated Table 58, page 46 to more closely match the DSP48E1 speed specifications. Updated T_{TAPTCK}/T_{TCKTAP} in Table 59, page 49. Updated XC6VLX130T parameters in Table 68 through Table 70, page 59.
08/19/09	1.2	Added values for -1L voltages and speed grade in all pertinent tables. Added V_{FS} and notes to Table 1 and Table 2. Removed DV_{PPIN} from the example in Figure 2. Added networking applications to Table 41, page 25. Changed and added to the block RAM F_{MAX} section in Table 57, page 44 including removing Note 12. Changed F_{PFDMAX} values and corrected units for $T_{STATPHAOFFSET}$ and $T_{OUTDUTY}$ in Table 64, page 52. Updated Table 71, page 60.
09/16/09	2.0	Added Virtex-6 HXT devices to entire document including GTH Transceiver Specifications. Updated speed specifications as described in Switching Characteristics, includes changes in Table 51, Table 57, Table 58, and Table 66 through Table 70. Comprehensive changes to Table 14, Table 15, and Table 16. Added conditions to D_{VPPOUT} and revised description of T_{OSKEW} in Table 17. Removed V_{ISE} specification and note from Table 18. Added note 3 to Table 23. Updated note 3 in Table 24. Updated LVCMOS25 delays in Table 44. Updated specification for T_{IOTPHZ} in Table 46. Removed $T_{BUFHSKEW}$ from Table 71, page 60 and added values for $T_{BUFIOSKEW}$. Added values in Table 74.